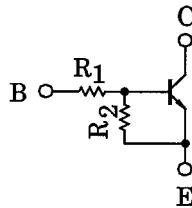


TOSHIBA Transistor Silicon NPN Epitaxial Type (PCT Process)

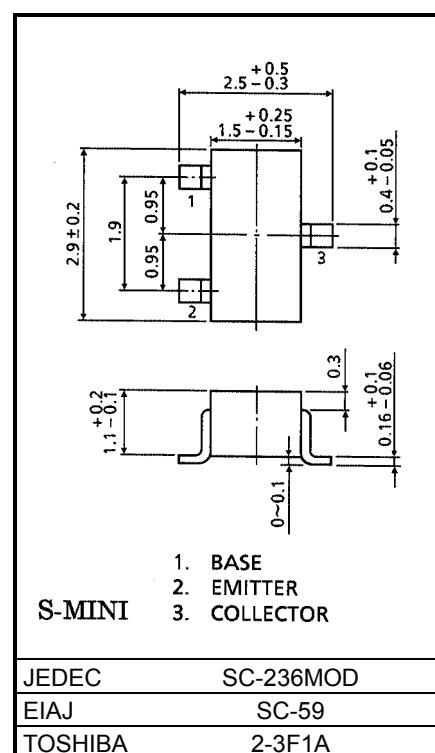
**RN1414,RN1415,RN1416
RN1417,RN1418**

Switching, Inverter Circuit, Interface Circuit
And Driver Circuit Applications

- With built-in bias resistors
- Simplify circuit design
- Reduce a quantity of parts and manufacturing process
- Complementary to RN2414~RN2418

Equivalent Circuit and Bias Resistor Values

Type No.	R1 (kΩ)	R2 (kΩ)
RN1414	1	10
RN1415	2.2	10
RN1416	4.7	10
RN1417	10	4.7
RN1418	47	10



Weight: 0.012g

Maximum Ratings (Ta = 25°C)

Characteristic		Symbol	Rating	Unit
Collector-base voltage	RN1414~1418	V _{CBO}	50	V
Collector-emitter voltage		V _{CEO}	50	V
Emitter-base voltage	RN1414 RN1415 RN1416 RN1417 RN1418	V _{EBO}	5	V
			6	
			7	
			15	
			25	
Collector current	RN1414~1418	I _C	100	mA
Collector power dissipation		P _C	200	mW
Junction temperature		T _j	150	°C
Storage temperature range		T _{stg}	-55~150	°C

Electrical Characteristics (Ta = 25°C)

Characteristic		Symbol	Test Circuit	Test Condition		Min	Typ.	Max	Unit
Collector cut-off current	RN1414~1418	I _{CBO}	—	V _{CB} = 50V, I _E = 0	V _{CE} = 50V, I _B = 0	—	—	100	nA
	RN1414~1418	I _{CEO}		V _{CB} = 50V, I _E = 0	V _{CE} = 50V, I _B = 0	—	—	500	nA
Emitter cut-off current	RN1414	I _{EBO}	—	V _{EB} = 5V, I _C = 0	V _{EB} = 6V, I _C = 0	0.35	—	0.65	mA
	RN1415			V _{EB} = 7V, I _C = 0	V _{EB} = 15V, I _C = 0	0.37	—	0.71	
	RN1416			V _{EB} = 25V, I _C = 0	V _{EB} = 25V, I _C = 0	0.36	—	0.68	
	RN1417			V _{EB} = 5V, I _C = 0	V _{EB} = 15V, I _C = 0	0.78	—	1.46	
	RN1418			V _{EB} = 25V, I _C = 0	V _{EB} = 25V, I _C = 0	0.33	—	0.63	
DC current gain	RN1414~16, 18	h _{FE}	—	V _{CE} = 5V, I _C = 10mA	50	—	—		
	RN1417				30	—	—		
Collector-emitter saturation voltage	RN1414~1418	V _{CE} (sat)	—	I _C = 5mA, I _B = 0.25mA	—	0.1	0.3	—	V
Input voltage (ON)	RN1414	V _I (ON)	—	V _{CE} = 0.2V, I _C = 5mA	0.6	—	2.0		V
	RN1415				0.7	—	2.5		
	RN1416				0.8	—	2.5		
	RN1417				1.5	—	3.5		
	RN1418				2.5	—	10.0		
Input voltage (OFF)	RN1414	V _I (OFF)	—	V _{CE} = 5V, I _C = 0.1mA	0.3	—	0.9		V
	RN1415				0.3	—	1.0		
	RN1416				0.3	—	1.1		
	RN1417				0.3	—	2.3		
	RN1418				0.5	—	5.7		
Transition frequency	RN1414~1418	f _T	—	V _{CE} = 10V, I _C = 5mA	—	250	—	MHz	
Collector Output capacitance	RN1414~1418	C _{ob}	—	V _{CB} = 10V, I _E = 0, f = 1MHz	—	3.0	6.0	pF	
Input resistor	RN1414	R1	—	—	0.7	1.0	1.3		kΩ
	RN1415				1.54	2.2	2.86		
	RN1416				3.29	4.7	6.11		
	RN1417				7.0	10.0	13.0		
	RN1418				32.9	47.0	61.1		
Resistor ratio	RN1414	R1/R2	—	—	—	0.1	—		
	RN1415				—	0.22	—		
	RN1416				—	0.47	—		
	RN1417				—	2.13	—		
	RN1418				—	4.7	—		

